

TOSHIBA**1SS369**

TOSHIBA DIODE SILICON EPITAXIAL SCHOTTKY BARRIER TYPE

1SS369

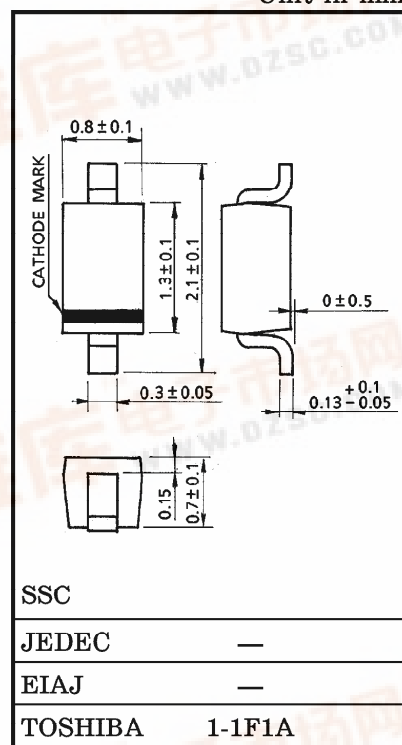
LOW VOLTAGE HIGH SPEED SWITCHING

Unit in mm

- Small Package
- Low Forward Voltage : $V_F(3)=0.54V$ (TYP.)
- Low Reverse Current : $I_R=5\mu A$ (MAX.)

MAXIMUM RATINGS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Maximum (Peak) Reverse Voltage	V_{RM}	45	V
Reverse Voltage	V_R	40	V
Maximum (Peak) Forward Current	I_{FM}	300	mA
Average Forward Current	I_O	100	mA
Surge Current (10ms)	I_{FSM}	1	A
Power Dissipation	P_{\ast}	150	mW
Junction Temperature	T_j	125	$^\circ C$
Storage Temperature Range	T_{stg}	$-55 \sim 125$	$^\circ C$
Operating Temperature Range	T_{opr}	$-40 \sim 100$	$^\circ C$



Weight : 1.9mg

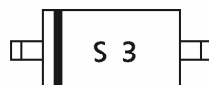
※ Mounted on a glass epoxy circuit board of 20×20mm, pad dimension of 4×4mm.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ C$)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Forward Voltage	$V_F(1)$	$I_F = 1mA$	—	0.28	—	V
	$V_F(2)$	$I_F = 10mA$	—	0.36	—	
	$V_F(3)$	$I_F = 100mA$	—	0.54	0.60	
Reverse Current	I_R	$V_R = 40V$	—	—	5	μA
Total Capacitance	C_T	$V_R = 0, f = 1MHz$	—	18	25	pF

PIN ASSIGNMENT (TOP VIEW)

MARKING



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